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Michel Haond, STMicroelectronics

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¹Device Modelling Group, School of Engineering, University of Glasgow, UK, ²Gold Standard Simulations Ltd (GSS).

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Electrical Engineering and Computer Sciences, University of California, Berkeley, USA

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¹Centro Universitário da FEI, ²Universidade Metodista de São Paulo, Brazil

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¹Electrical Engineering and Computer Sciences, University of California, Berkeley, USA, ²University of Seoul, Korea, ³CEA-LETI, ⁴AMD GmbH, ⁵CEA-LIST, ⁶Synopsys (invited talk)

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¹ICTEAM Institute, Université catholique de Louvain, Belgium, ²CEA-LETI, MINATEC

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